

Designer's™ Data Sheet

SWITCHMODE™

NPN Bipolar Power Transistor

For Switching Power Supply Applications

The MJE/MJF18002 have an applications specific state-of-the-art die designed for use in 220 V line operated Switchmode Power supplies and electronic light ballasts. These high voltage/high speed transistors offer the following:

- Improved Efficiency Due to Low Base Drive Requirements:
 - High and Flat DC Current Gain h_{FE}
 - Fast Switching
 - No Coil Required in Base Circuit for Turn-Off (No Current Tail)
- Tight Parametric Distributions are Consistent Lot-to-Lot
- Two Package Choices: Standard TO-220 or Isolated TO-220
- MJF18002, Case 221D, is UL Recognized at 3500 V_{RMS}: File #E69369

MAXIMUM RATINGS

Rating	Symbol	MJE18002	MJF18002	Unit
Collector-Emitter Sustaining Voltage	V_{CEO}	450		V _{dc}
Collector-Emitter Breakdown Voltage	V_{CES}	1000		V _{dc}
Emitter-Base Voltage	V_{EBO}	9.0		V _{dc}
Collector Current — Continuous	I_C	2.0		A _{dc}
— Peak(1)	I_{CM}	5.0		
Base Current — Continuous	I_B	1.0		A _{dc}
— Peak(1)	I_{BM}	2.0		
RMS Isolated Voltage(2)	V_{ISOL}	—	4500	V
(for 1 sec, R.H. < 30%, $T_C = 25^\circ\text{C}$)		—	3500	
Test No. 1 Per Fig. 1		—	1500	
Test No. 2 Per Fig. 2				
Test No. 3 Per Fig. 3				
Total Device Dissipation ($T_C = 25^\circ\text{C}$)	P_D	50	25	Watts
Derate above 25°C		0.4	0.2	W/ $^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{stg}	-65 to 150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Rating	Symbol	MJE18002	MJF18002	Unit
Thermal Resistance — Junction to Case	$R_{\theta JC}$	2.5	5.0	$^\circ\text{C/W}$
— Junction to Ambient	$R_{\theta JA}$	62.5	62.5	
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T_L	260		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage ($I_C = 100\text{ mA}$, $L = 25\text{ mH}$)	$V_{CEO(sus)}$	450	—	—	V _{dc}
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $I_B = 0$)	I_{CEO}	—	—	100	μA_{dc}
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CES}$, $V_{EB} = 0$) ($V_{CE} = 800\text{ V}$, $V_{EB} = 0$)	I_{CES}	$T_C = 125^\circ\text{C}$		100	μA_{dc}
		$T_C = 125^\circ\text{C}$		500	
				100	
Emitter Cutoff Current ($V_{EB} = 9.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	—	100	μA_{dc}

(1) Pulse Test: Pulse Width = 5.0 ms, Duty Cycle $\leq 10\%$.

(2) Proper strike and creepage distance must be provided.

(continued)

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

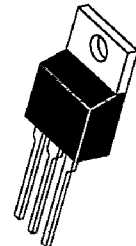
Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1

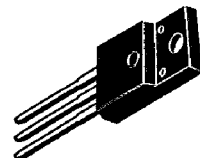
MJE18002*
MJF18002*

*Motorola Preferred Device

POWER TRANSISTOR
2.0 AMPERES
1000 VOLTS
25 and 50 WATTS



CASE 221A-06
TO-220AB
MJE18002



CASE 221D-02
ISOLATED TO-220 TYPE
UL RECOGNIZED
MJF18002

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
Base-Emitter Saturation Voltage ($I_C = 0.4\text{ Adc}$, $I_B = 40\text{ mAdc}$) ($I_C = 1.0\text{ Adc}$, $I_B = 0.2\text{ Adc}$)	$V_{BE(sat)}$	— —	0.825 0.92	1.1 1.25	Vdc
Collector-Emitter Saturation Voltage ($I_C = 0.4\text{ Adc}$, $I_B = 40\text{ mAdc}$) ($I_C = 1.0\text{ Adc}$, $I_B = 0.2\text{ Adc}$)	$V_{CE(sat)}$	— — — —	0.2 0.2 0.25 0.3	0.5 0.5 0.5 0.6	Vdc
DC Current Gain ($I_C = 0.2\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 0.4\text{ Adc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 1.0\text{ Adc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	14 — 11 11 6.0 5.0 10	— 27 17 20 8.0 8.0 20	34 — — — — — —	—

DYNAMIC CHARACTERISTICS

Current Gain Bandwidth ($I_C = 0.2\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ MHz}$)	f_T	—	13	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	—	35	60	pF
Input Capacitance ($V_{EB} = 8.0\text{ V}$)	C_{ib}	—	400	600	pF
Dynamic Saturation: determined 1.0 μs and 3.0 μs after rising I_{B1} reach 0.9 final I_{B1} (see Figure 18)	$I_C = 0.4\text{ A}$ $I_{B1} = 40\text{ mA}$ $V_{CC} = 300\text{ V}$	1.0 μs 3.0 μs	@ $T_C = 125^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	$V_{CE(dsat)}$	— — — — — — — —
	$I_C = 1.0\text{ A}$ $I_{B1} = 0.2\text{ A}$ $V_{CC} = 300\text{ V}$	1.0 μs 3.0 μs	@ $T_C = 125^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$		3.5 8.0 1.5 3.8 8.0 14 2.0 7.0

SWITCHING CHARACTERISTICS: Resistive Load ($D.C. \leq 10\%$, Pulse Width = 20 μs)

Turn-On Time	$I_C = 0.4\text{ Adc}$ $I_{B1} = 40\text{ mAdc}$	@ $T_C = 125^\circ\text{C}$	t_{on}	— —	200 130	300 —	ns
Turn-Off Time	$I_{B2} = 0.2\text{ Adc}$ $V_{CC} = 300\text{ V}$	@ $T_C = 125^\circ\text{C}$	t_{off}	— —	1.2 1.5	2.5 —	μs
Turn-On Time	$I_C = 1.0\text{ Adc}$ $I_{B1} = 0.2\text{ Adc}$	@ $T_C = 125^\circ\text{C}$	t_{on}	— —	85 95	150 —	ns
Turn-Off Time	$I_{B2} = 0.5\text{ Adc}$ $V_{CC} = 300\text{ V}$	@ $T_C = 125^\circ\text{C}$	t_{off}	— —	1.7 2.1	2.5 —	μs

SWITCHING CHARACTERISTICS: Inductive Load ($V_{clamp} = 300\text{ V}$, $V_{CC} = 15\text{ V}$, $L = 200\text{ }\mu\text{H}$)

Fall Time	$I_C = 0.4\text{ Adc}$, $I_{B1} = 40\text{ mAdc}$, $I_{B2} = 0.2\text{ Adc}$	@ $T_C = 125^\circ\text{C}$	t_{fi}	— —	125 120	200 —	ns
Storage Time		@ $T_C = 125^\circ\text{C}$	t_{si}	— —	0.7 0.8	1.25 —	μs
Crossover Time		@ $T_C = 125^\circ\text{C}$	t_c	— —	110 110	200 —	ns
Fall Time	$I_C = 1.0\text{ Adc}$, $I_{B1} = 0.2\text{ Adc}$, $I_{B2} = 0.5\text{ Adc}$	@ $T_C = 125^\circ\text{C}$	t_{fi}	— —	110 120	175 —	ns
Storage Time		@ $T_C = 125^\circ\text{C}$	t_{si}	— —	1.7 2.25	2.75 —	μs
Crossover Time		@ $T_C = 125^\circ\text{C}$	t_c	— —	200 250	300 —	ns
Fall Time	$I_C = 0.4\text{ Adc}$, $I_{B1} = 50\text{ mAdc}$, $I_{B2} = 50\text{ mAdc}$	@ $T_C = 125^\circ\text{C}$	t_{fi}	— —	140 185	200 —	ns
Storage Time		@ $T_C = 125^\circ\text{C}$	t_{si}	— —	2.2 2.5	3.0 —	μs
Crossover Time		@ $T_C = 125^\circ\text{C}$	t_c	— —	140 220	250 —	ns

TYPICAL STATIC CHARACTERISTICS

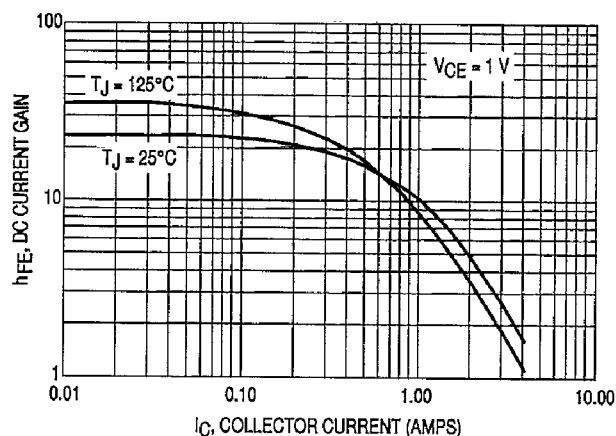


Figure 1. DC Current Gain @ 1 Volt

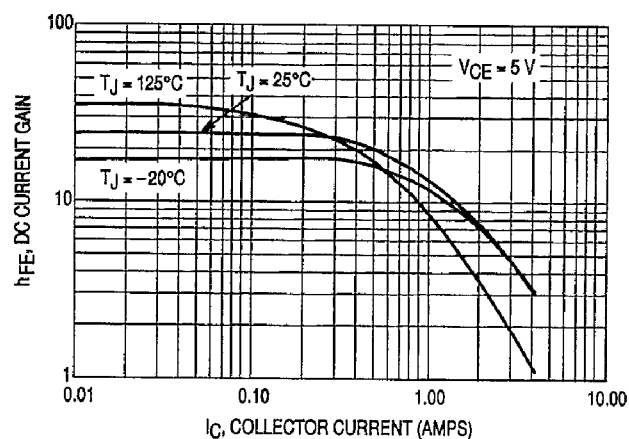


Figure 2. DC Current Gain @ 5 Volts

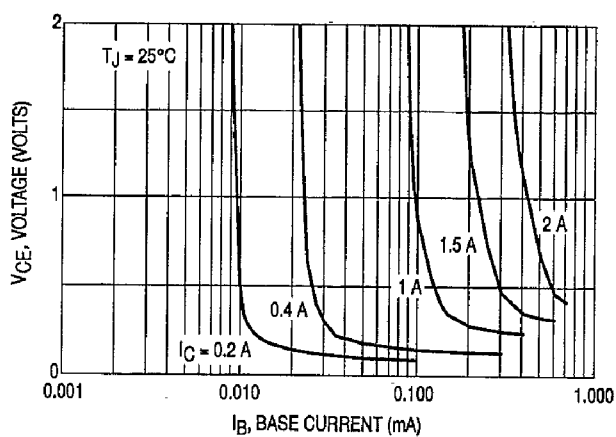


Figure 3. Collector Saturation Region

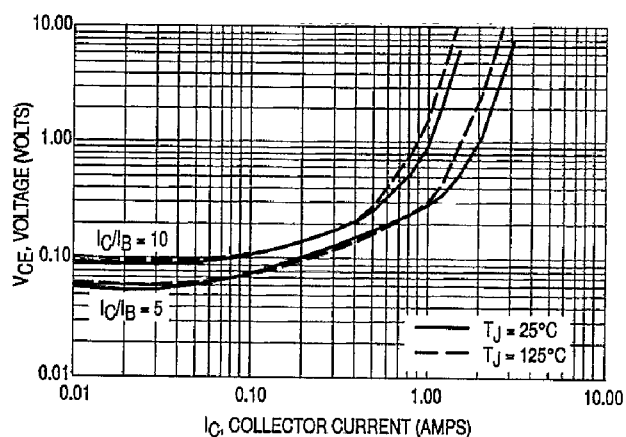


Figure 4. Collector-Emitter Saturation Voltage

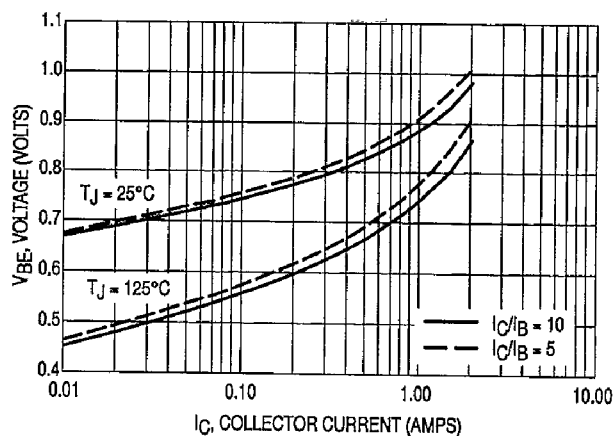


Figure 5. Base-Emitter Saturation Region

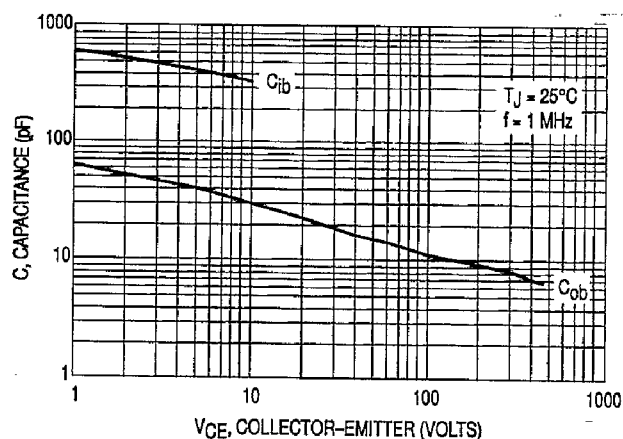


Figure 6. Capacitance

TYPICAL SWITCHING CHARACTERISTICS ($I_{B2} = I_C/2$ for all switching)

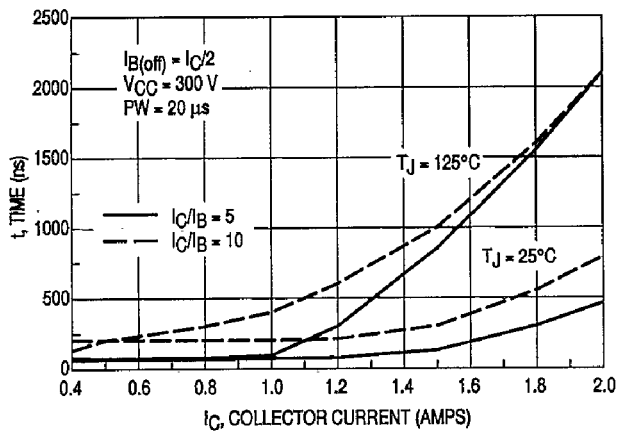
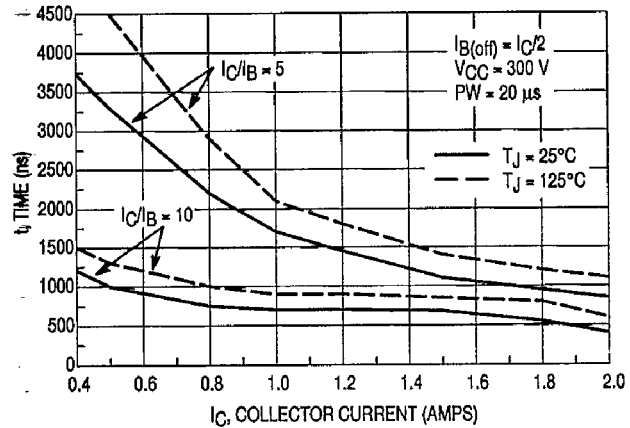
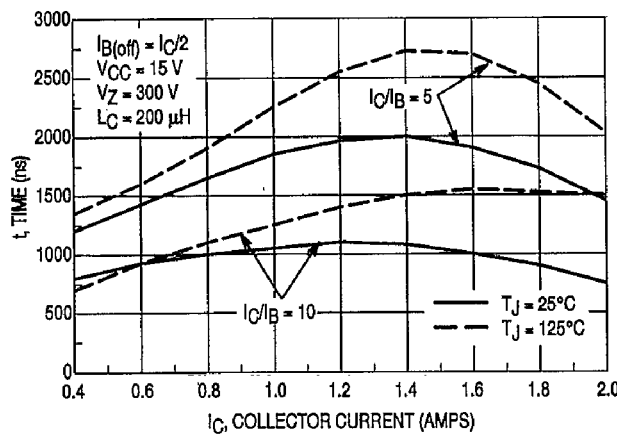
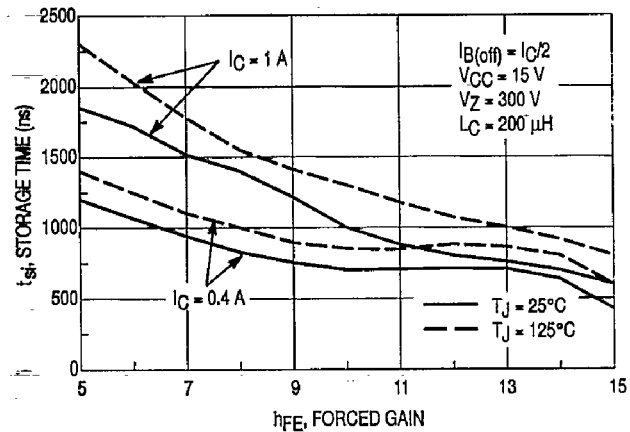
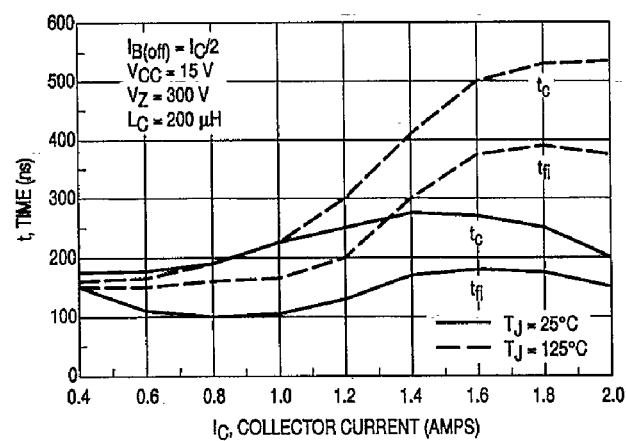
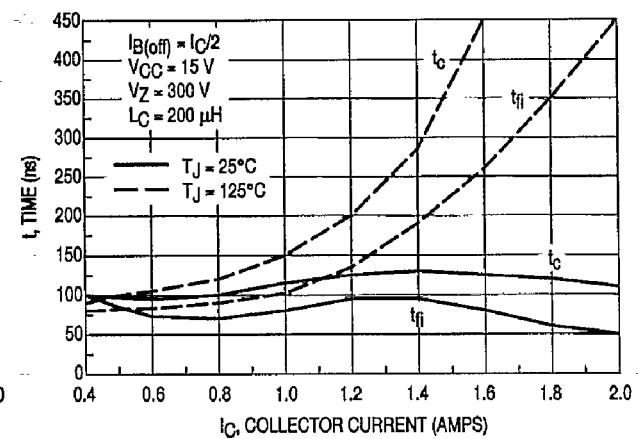
Figure 7. Resistive Switching, t_{on} Figure 8. Resistive Switching, t_{off} Figure 9. Inductive Storage Time, t_{si} 

Figure 10. Inductive Storage Time

Figure 11. Inductive Switching, t_c & t_{fi} , $I_C/I_B = 5$ Figure 12. Inductive Switching, t_c & t_{fi} , $I_C/I_B = 10$

TYPICAL SWITCHING CHARACTERISTICS
($I_{B2} = I_C/2$ for all switching)

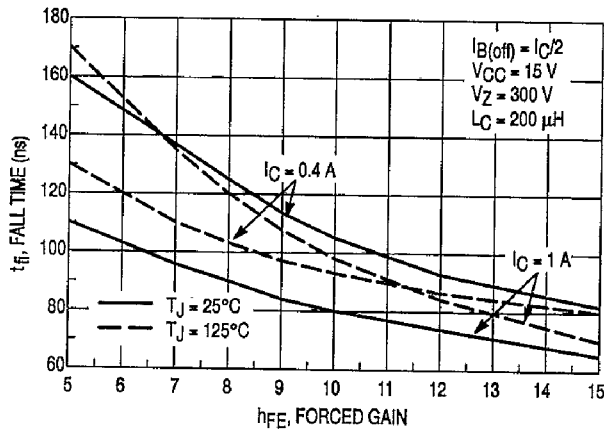


Figure 13. Inductive Fall Time

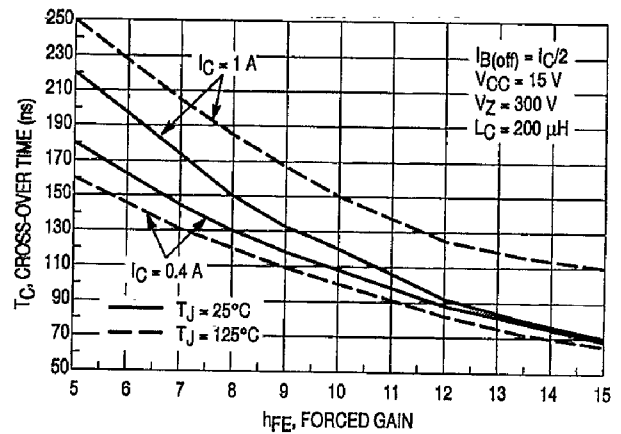


Figure 14. Inductive Crossover Time

GUARANTEED SAFE OPERATING AREA INFORMATION

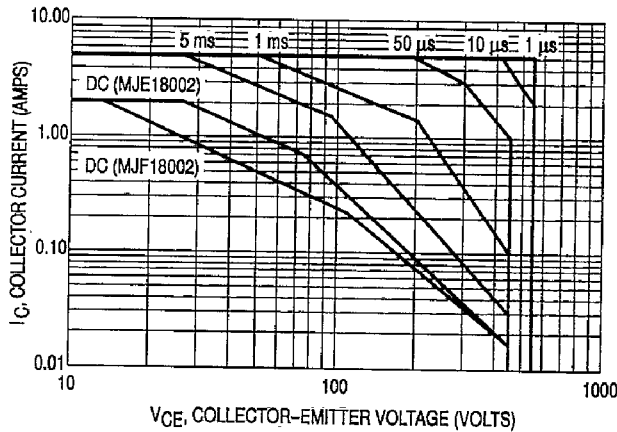


Figure 15. Forward Bias Safe Operating Area

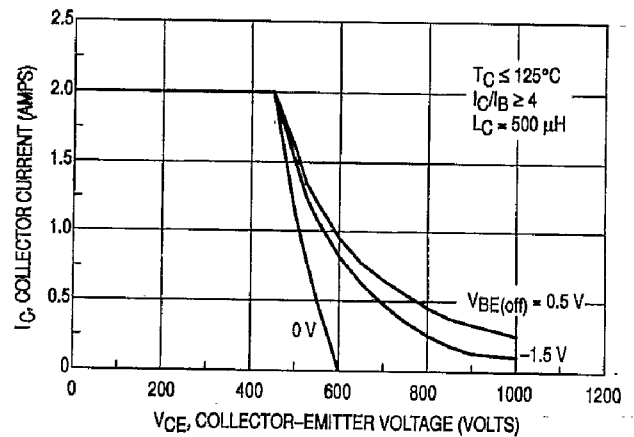


Figure 16. Reverse Bias Switching Safe Operating Area

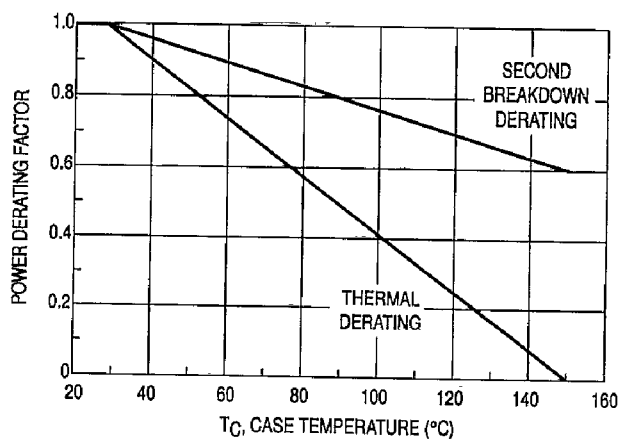


Figure 17. Forward Bias Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 15 is based on $T_C = 25^\circ\text{C}$; $T_J(\text{pk})$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C > 25^\circ\text{C}$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 15 may be found at any case temperature by using the appropriate curve on Figure 17. $T_J(\text{pk})$ may be calculated from the data in Figures 20 and 21. At any case temperatures, thermal limitations will reduce the power that can be handled to values less the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn-off with the base to emitter junction reverse biased. The safe level is specified as a reverse biased safe operating area (Figure 16). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

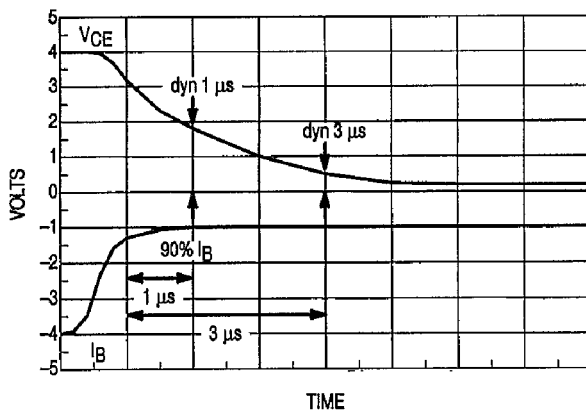


Figure 18. Dynamic Saturation Voltage Measurements

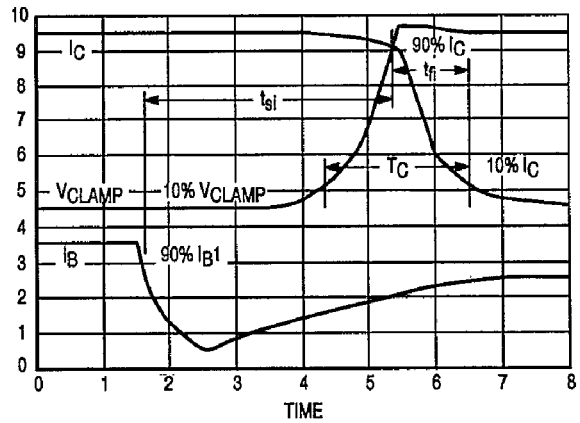
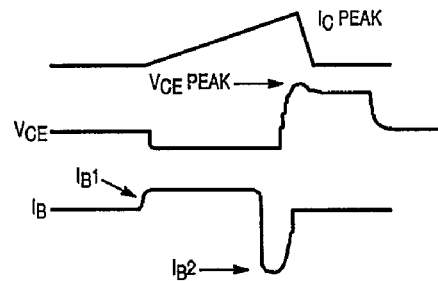
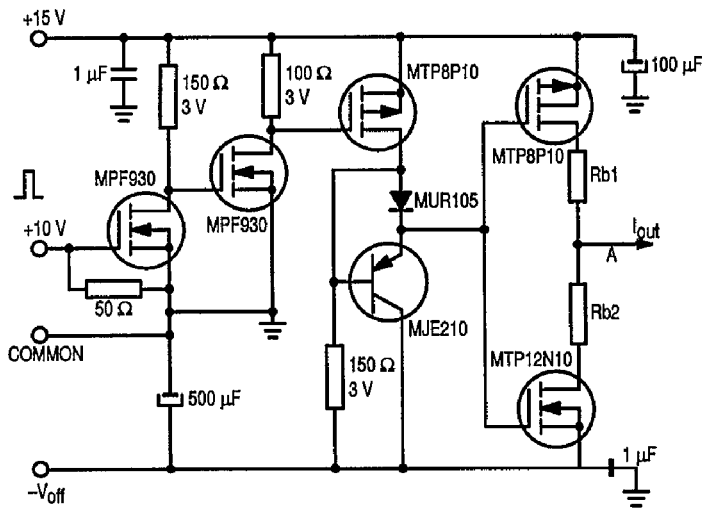


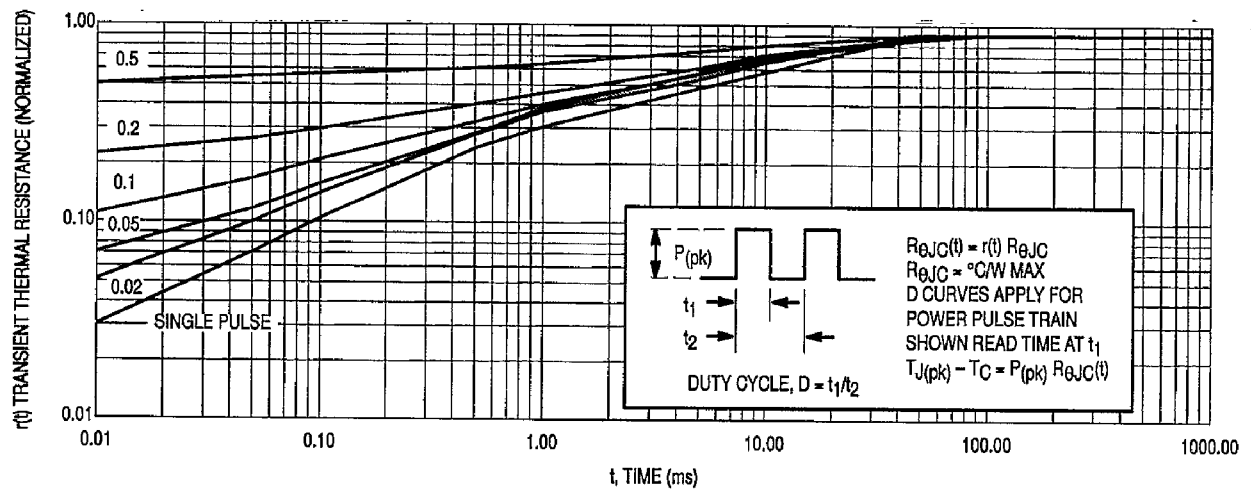
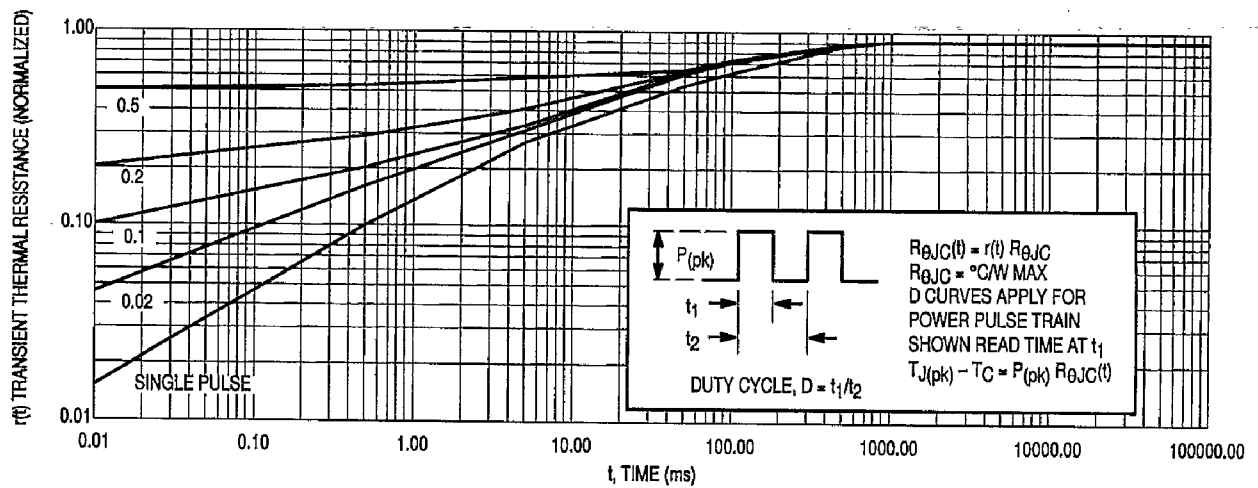
Figure 19. Inductive Switching Measurements



V(BR)CEO(sus)	INDUCTIVE SWITCHING	RBSOA
L = 10 μH	L = 200 μH	L = 500 μH
RB2 = ∞	RB2 = 0	RB2 = 0
VCC = 20 VOLTS	VCC = 15 VOLTS	VCC = 15 VOLTS
IC(pk) = 100 mA	RB1 SELECTED FOR DESIRED IB1	RB1 SELECTED FOR DESIRED IB1

Table 1. Inductive Load Switching Drive Circuit

TYPICAL THERMAL RESPONSE

Figure 20. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJE18002Figure 21. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJF18002

TEST CONDITIONS FOR ISOLATION TESTS*

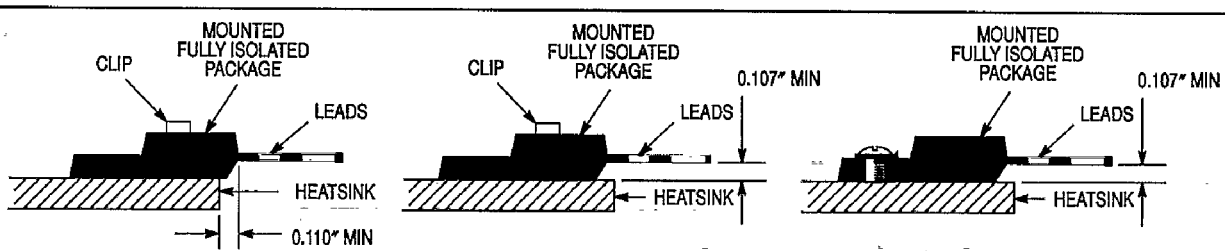


Figure 22a. Screw or Clip Mounting Position for Isolation Test Number 1

Figure 22b. Clip Mounting Position for Isolation Test Number 2

Figure 22c. Screw Mounting Position for Isolation Test Number 3

* Measurement made between leads and heatsink with all leads shorted together

MOUNTING INFORMATION**

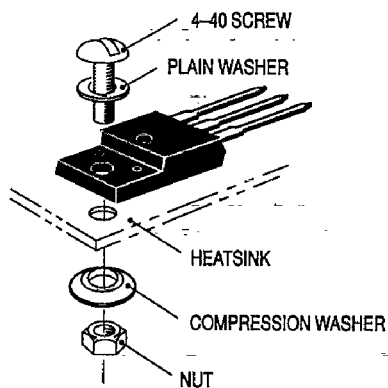


Figure 23a. Screw-Mounted

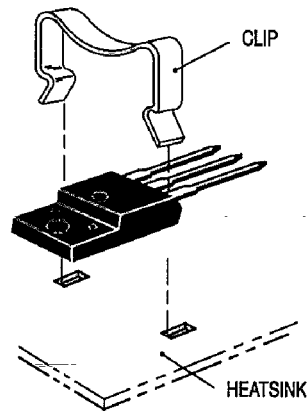


Figure 23b. Clip-Mounted

Figure 23. Typical Mounting Techniques for Isolated Package

Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in · lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4-40 screw, without washers, and applying a torque in excess of 20 in · lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

Additional tests on slotted 4-40 screws indicate that the screw slot fails between 15 to 20 in · lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, Motorola does not recommend exceeding 10 in · lbs of mounting torque under any mounting conditions.

** For more information about mounting power semiconductors see Application Note AN1040.